

General Purpose Transistors

NPN Silicon

BC846ALT1G Series

Features

- Moisture Sensitivity Level: 1
- ESD Rating Human Body Model: > 4000 V
 - Machine Model: > 400 V
- S and NSV Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q101 Qualified and PPAP Capable
- These Devices are Pb–Free, Halogen Free/BFR Free and are RoHS Compliant

MAXIMUM RATINGS

Rating		Symbol	Value	Unit
Collector-Emitter Voltage	BC846 BC847, BC850 BC848, BC849	V _{CEO}	65 45 30	Vdc
Collector-Base Voltage	BC846 BC847, BC850 BC848, BC849	V _{CBO}	80 50 30	Vdc
Emitter-Base Voltage	BC846 BC847, BC850 BC848, BC849	V _{EBO}	6.0 6.0 5.0	Vdc
Collector Current – Continuous		I _C	100	mAdc

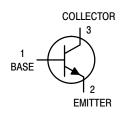
Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Total Device Dissipation FR-5 Board, (Note 1) T _A = 25°C Derate above 25°C	P _D	225	mW mW/°C
Derate above 25 C		1.0	IIIVV/ C
Thermal Resistance, Junction-to-Ambient (Note 1)	$R_{ heta JA}$	556	°C/W
Total Device Dissipation Alumina Substrate (Note 2) T _A = 25°C Derate above 25°C	P _D	300	mW mW/°C
Derate above 25°C		2.4	IIIVV/°C
Thermal Resistance, Junction-to-Ambient (Note 2)	$R_{\theta JA}$	417	°C/W
Junction and Storage Temperature Range	T _J , T _{stg}	-55 to +150	°C

1

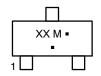
- 1. FR-5 = $1.0 \times 0.75 \times 0.062$ in.
- 2. Alumina = 0.4 \times 0.3 \times 0.024 in 99.5% alumina.





SOT-23 CASE 318 STYLE 6

MARKING DIAGRAM



XX = Device CodeM = Date Code*= Pb-Free Package

(Note: Microdot may be in either location)

*Date Code orientation and/or overbar may vary depending upon manufacturing location.

ORDERING INFORMATION

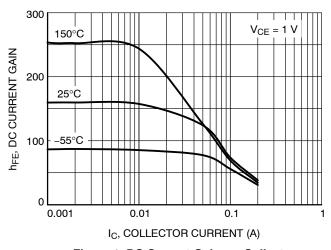
See detailed ordering and shipping information in the package dimensions section on page 12 of this data sheet.

ELECTRICAL CHARACTERISTICS ($T_A = 25^{\circ}C$ unless otherwise noted)

Characteris	Symbol	Min	Тур	Max	Unit	
OFF CHARACTERISTICS			•		•	•
Collector – Emitter Breakdown Voltage (I _C = 10 mA)	BC846A, B, C BC847A, B, C, BC850B, C BC848A, B, C, BC849B, C	V _{(BR)CEO}	65 45 30	- - -	- - -	V
Collector – Emitter Breakdown Voltage ($I_C = 10 \mu A, V_{EB} = 0$)	BC846A, B, C BC847A, B, C BC850B, C BC848A, B, C, BC849B, C	V _{(BR)CES}	80 50 30	- - -	- - -	V
Collector – Base Breakdown Voltage ($I_C = 10 \mu A$)	BC846A, B, C BC847A, B, C, BC850B, C BC848A, B, C, BC849B, C	V _{(BR)CBO}	80 50 30	- - -	- - -	V
Emitter – Base Breakdown Voltage ($I_E = 1.0 \mu A$)	BC846A, B, C BC847A, B, C, BC850B, C BC848A, B, C, BC849B, C	V _{(BR)EBO}	6.0 6.0 5.0	- - -	- - -	V
Collector Cutoff Current (V _{CB} = 30 V) (V _{CB} = 30 V, T _A = 150°C)	I _{CBO}	- -	- -	15 5.0	nA μA	
ON CHARACTERISTICS						
DC Current Gain ($I_C = 10 \mu A$, $V_{CE} = 5.0 V$)	BC846A, BC847A, BC848A BC846B, BC847B, BC848B BC846C, BC847C, BC848C	h _{FE}	- - -	90 150 270	- - -	-
$(I_C = 2.0 \text{ mA}, V_{CE} = 5.0 \text{ V})$	BC846A, BC847A, BC848A BC846B, BC847B, BC848B, BC849B, BC850B		110 200	180 290	220 450	
BC846C, BC847C, BC848C, BC849C, BC850C			420	520	800	
Collector – Emitter Saturation Voltage ($I_C = \frac{1}{2}$)	10 mA, I _B = 0.5 mA) 100 mA, I _B = 5.0 mA)	V _{CE(sat)}	- -	- -	0.25 0.6	V
Base – Emitter Saturation Voltage ($I_C = 10 \text{ n}$) ($I_C = 100 \text{ m}$)	nA, I _B = 0.5 mA) mA, I _B = 5.0 mA)	V _{BE(sat)}	- -	0.7 0.9	- -	V
Base – Emitter Voltage (I_C = 2.0 mA, V_{CE} = 5.0 V) (I_C = 10 mA, V_{CE} = 5.0 V)			580 -	660 -	700 770	mV
SMALL-SIGNAL CHARACTERISTICS				-		
Current – Gain – Bandwidth Product ($I_C = 10 \text{ mA}, V_{CE} = 5.0 \text{ Vdc}, f = 100 \text{ MHz}$)			100	_	-	MHz
Output Capacitance (V _{CB} = 10 V, f = 1.0 MHz)			_	-	4.5	pF
Noise Figure (I_C = 0.2 mA, V_{CE} = 5.0 Vdc, R_S = 2.0 k Ω , I_S = 0.0 Hz) BC846A,B,C, BC847A,B,C, BC848A,B,C BC849B,C, BC850B,C			- -	_ _	10 4.0	dB

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

BC846A, BC847A, BC848A, SBC846A



300 150°C VCE = 5 V VCE = 5 V 200 25°C 100 --55°C 0 0.001 0.01 1c, COLLECTOR CURRENT (A)

Figure 1. DC Current Gain vs. Collector Current

Figure 2. DC Current Gain vs. Collector Current

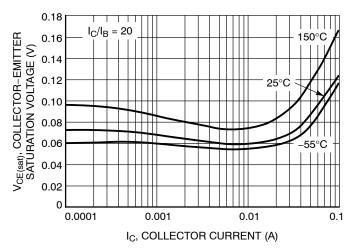


Figure 3. Collector Emitter Saturation Voltage vs. Collector Current

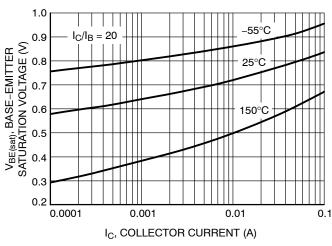


Figure 4. Base Emitter Saturation Voltage vs.
Collector Current

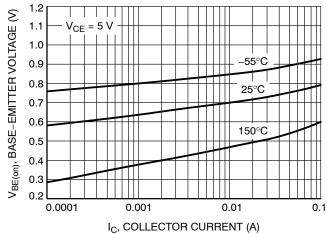
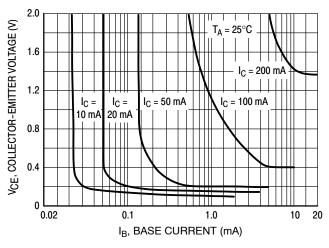


Figure 5. Base Emitter Voltage vs. Collector Current

BC846A, BC847A, BC848A, SBC846A



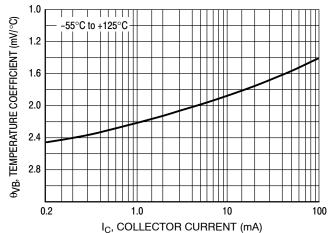
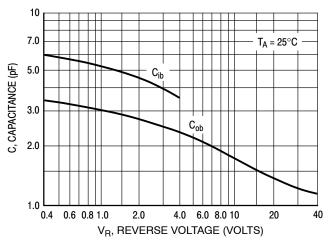


Figure 6. Collector Saturation Region

Figure 7. Base-Emitter Temperature Coefficient





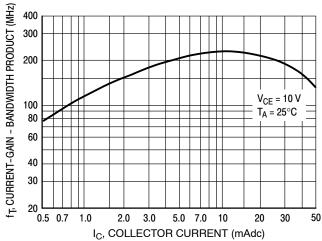


Figure 9. Current-Gain - Bandwidth Product

BC846B, SBC846B

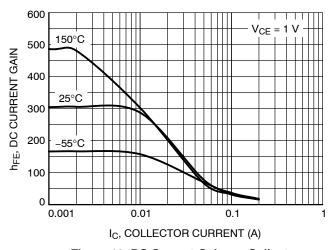


Figure 10. DC Current Gain vs. Collector Current

Figure 11. DC Current Gain vs. Collector Current

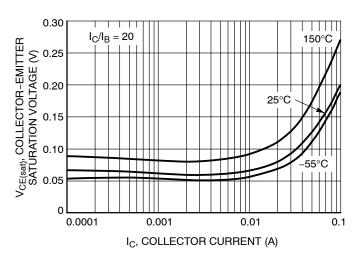


Figure 12. Collector Emitter Saturation Voltage vs. Collector Current

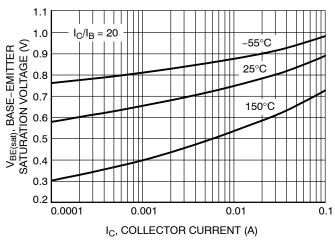


Figure 13. Base Emitter Saturation Voltage vs. Collector Current

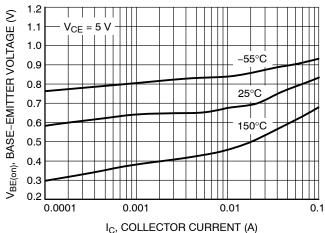
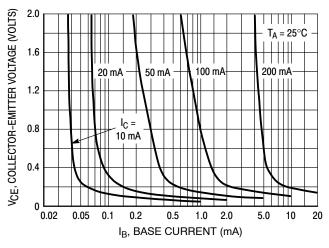


Figure 14. Base Emitter Voltage vs. Collector Current

BC846B, SBC846B



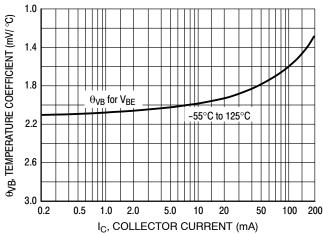


Figure 15. Collector Saturation Region

Figure 16. Base-Emitter Temperature Coefficient

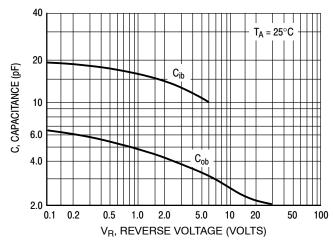


Figure 17. Capacitance

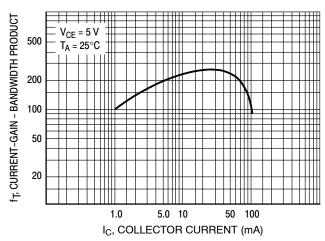
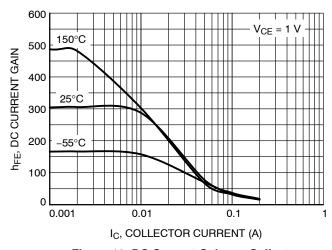


Figure 18. Current-Gain - Bandwidth Product

BC847B, BC848B, BC849B, BC850B, SBC847B, SBC848B



600 $V_{CE} = 5 V$ 150°C 500 h_{FE}, DC CURRENT GAIN 400 25°C 300 200 -55°C 100 0 0.001 0.01 0.1 I_C, COLLECTOR CURRENT (A)

Figure 19. DC Current Gain vs. Collector Current

Figure 20. DC Current Gain vs. Collector Current

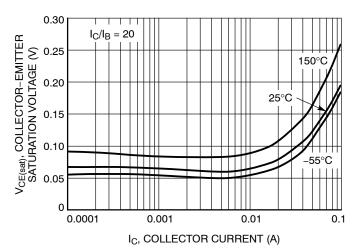
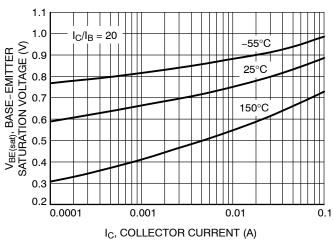


Figure 21. Collector Emitter Saturation Voltage vs. Collector Current





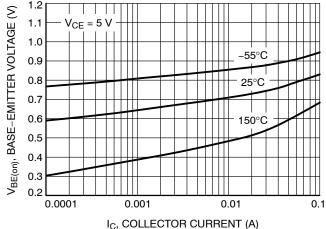


Figure 23. Base Emitter Voltage vs. Collector Current

BC847B, BC848B, BC849B, BC850B, SBC846B, SBC847B, SBC848B

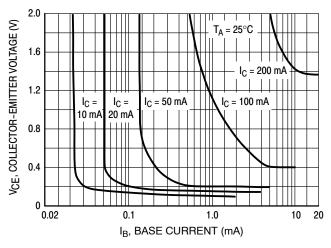


Figure 24. Collector Saturation Region

Figure 25. Base–Emitter Temperature Coefficient

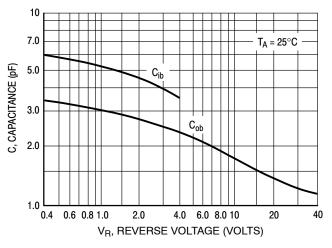


Figure 26. Capacitances

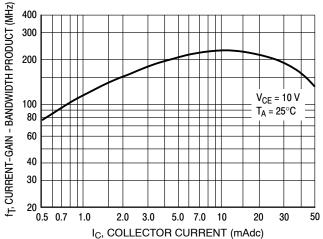
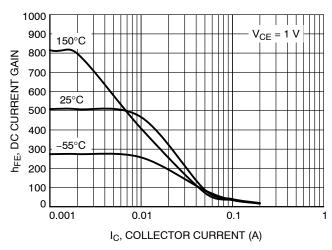


Figure 27. Current-Gain - Bandwidth Product

BC846C, BC847C, BC848C, BC849C, BC850C, SBC847C



1000 900 150°C V_{CE} 800 hFE, DC CURRENT GAIN 700 600 25°C 500 400 -55°C 300 200 100 0.001 0.01 0.1 IC, COLLECTOR CURRENT (A)

Figure 28. DC Current Gain vs. Collector Current

Figure 29. DC Current Gain vs. Collector Current

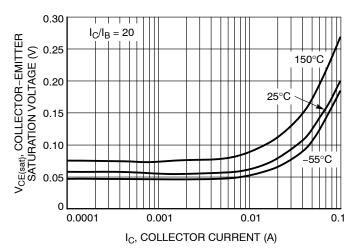


Figure 30. Collector Emitter Saturation Voltage vs. Collector Current

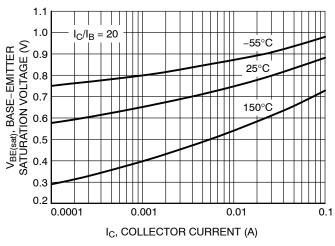


Figure 31. Base Emitter Saturation Voltage vs. Collector Current

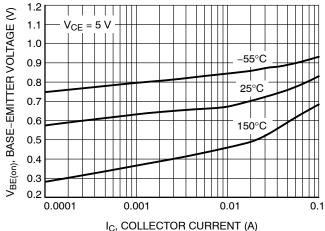


Figure 32. Base Emitter Voltage vs. Collector Current

BC846C, BC847C, BC848C, BC849C, BC850C, SBC847C

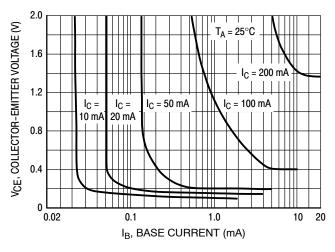
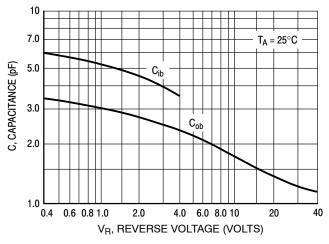


Figure 33. Collector Saturation Region

Figure 34. Base–Emitter Temperature Coefficient



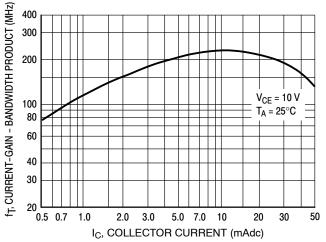


Figure 35. Capacitances

Figure 36. Current-Gain - Bandwidth Product

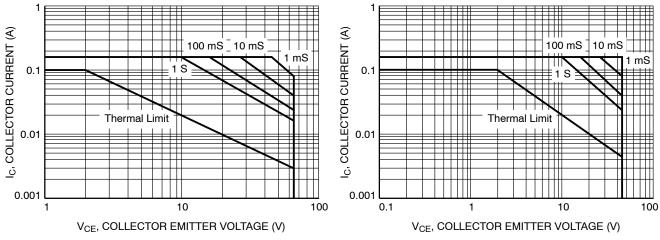


Figure 37. Safe Operating Area for BC846A, BC846B, BC846C

Figure 38. Safe Operating Area for BC847A, BC847B, BC847C, BC850B, BC850C

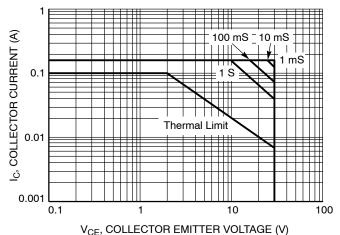


Figure 39. Safe Operating Area for BC848A, BC848B, BC848C, BC849B, BC849C

ORDERING INFORMATION

Device	Marking	Package	Shipping [†]			
BC846ALT1G						
SBC846ALT1G*	1A		3,000 / Tape & Reel			
BC846ALT3G			10,000 / Tape & Reel			
BC846BLT1G		1	0.000 / T			
SBC846BLT1G*	45		3,000 / Tape & Reel			
BC846BLT3G	1B		10 000 /T 0 D 1			
SBC846BLT3G*			10,000 / Tape & Reel			
BC846CLT1G	3C	1	3,000 / Tape & Reel			
BC847ALT1G			3,000 / Tape & Reel			
BC847ALT3G	1E		10,000 / Tape & Reel			
BC847BLT1G			0.000 / T			
SBC847BLT1G*			3,000 / Tape & Reel			
BC847BLT3G	1F					
NSVBC847BLT3G*			10,000 / Tape & Reel			
BC847CLT1G		1				
SBC847CLT1G*	1G		3,000 / Tape & Reel			
BC847CLT3G		SOT-23 (Pb-Free)	10,000 / Tape & Reel			
BC848ALT1G	1J	(. 5 5)	3,000 / Tape & Reel			
BC848BLT1G		1				
SBC848BLT1G*	1K		3,000 / Tape & Reel			
BC848BLT3G			10,000 / Tape & Reel			
BC848CLT1G			0.000 /T 0.D /			
NSVBC848CLT1G*	1L		3,000 / Tape & Reel			
BC848CLT3G			10,000 / Tape & Reel			
BC849BLT1G			0.000 /T 0 P I			
NSVBC849BLT1G*	2B		3,000 / Tape & Reel			
BC849BLT3G			10,000 / Tape & Reel			
BC849CLT1G		1	3,000 / Tape & Reel			
BC849CLT3G	2C		10,000 / Tape & Reel			
BC850BLT1G	0.5					
NSVBC850BLT1G*	2F		0.000 / Table 2. Dead			
BC850CLT1G	20		3,000 / Tape & Reel			
NSVBC850CLT1G*	2G					

[†]For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

^{*}S and NSV Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q101 Qualified and PPAP Capable.

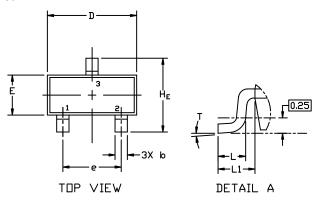




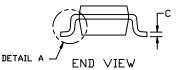
SOT-23 (TO-236) CASE 318 ISSUE AT

DATE 01 MAR 2023

SCALE 4:1





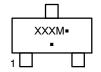


NOTES:

- DIMENSIONING AND TOLERANCING PER ASME Y14.5M,1994.
- 2. CONTROLLING DIMENSION: MILLIMETERS
- 3. MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF THE BASE MATERIAL.
- 4. DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR GATE BURRS.

	MILLIMETERS			INCHES		
DIM	MIN.	N□M.	MAX.	MIN.	N□M.	MAX.
Α	0.89	1.00	1.11	0.035	0.039	0.044
A1	0.01	0.06	0.10	0.000	0.002	0.004
b	0.37	0.44	0.50	0.015	0.017	0.020
С	0.08	0.14	0.20	0.003	0.006	0.008
D	2.80	2.90	3.04	0.110	0.114	0.120
Ε	1.20	1.30	1.40	0.047	0.051	0.055
e	1.78	1.90	2.04	0.070	0.075	0.080
L	0.30	0.43	0.55	0.012	0.017	0.022
L1	0.35	0.54	0.69	0.014	0.021	0.027
HE	2.10	2.40	2.64	0.083	0.094	0.104
Т	0*		10°	0*		10°

GENERIC MARKING DIAGRAM*

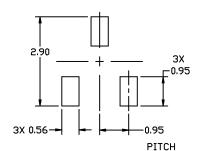


XXX = Specific Device Code

M = Date Code

■ = Pb-Free Package

*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "•", may or may not be present. Some products may not follow the Generic Marking.



RECOMMENDED MOUNTING FOOTPRINT

For additional information on our Pb-Free strategy and soldering details, please download the DN Semiconductor Soldering and Mounting Techniques Reference Manual, SDLDERRM/D.

STYLES ON PAGE 2

DOCUMENT NUMBER:	98ASB42226B	Electronic versions are uncontrolled except when accessed directly from the Document Repos Printed versions are uncontrolled except when stamped "CONTROLLED COPY" in red.		
DESCRIPTION:	SOT-23 (TO-236)		PAGE 1 OF 2	

onsemi and ONSEMI are trademarks of Semiconductor Components Industries, LLC dba onsemi or its subsidiaries in the United States and/or other countries. onsemi reserves the right to make changes without further notice to any products herein. onsemi makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does onsemi assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. onsemi does not convey any license under its patent rights nor the rights of others.

MECHANICAL CASE OUTLINE PACKAGE DIMENSIONS



SOT-23 (TO-236) CASE 318 ISSUE AT

DATE 01 MAR 2023

STYLE 1 THRU 5: CANCELLED	STYLE 6: PIN 1. BASE 2. EMITTER 3. COLLECTOR	STYLE 7: PIN 1. EMITTER 2. BASE 3. COLLECTOR	STYLE 8: PIN 1. ANODE 2. NO CONNECTION 3. CATHODE	ı	
STYLE 9: PIN 1. ANODE 2. ANODE 3. CATHODE	STYLE 10: PIN 1. DRAIN 2. SOURCE 3. GATE	STYLE 11: PIN 1. ANODE 2. CATHODE 3. CATHODE-ANODE	STYLE 12: PIN 1. CATHODE 2. CATHODE 3. ANODE	STYLE 13: PIN 1. SOURCE 2. DRAIN 3. GATE	STYLE 14: PIN 1. CATHODE 2. GATE 3. ANODE
STYLE 15: PIN 1. GATE 2. CATHODE 3. ANODE	STYLE 16: PIN 1. ANODE 2. CATHODE 3. CATHODE	STYLE 17: PIN 1. NO CONNECTION 2. ANODE 3. CATHODE	STYLE 18: PIN 1. NO CONNECTION 2. CATHODE 3. ANODE	STYLE 19: I PIN 1. CATHODE 2. ANODE 3. CATHODE-ANODE	STYLE 20: PIN 1. CATHODE 2. ANODE 3. GATE
STYLE 21: PIN 1. GATE 2. SOURCE 3. DRAIN	STYLE 22: PIN 1. RETURN 2. OUTPUT 3. INPUT	STYLE 23: PIN 1. ANODE 2. ANODE 3. CATHODE	STYLE 24: PIN 1. GATE 2. DRAIN 3. SOURCE	STYLE 25: PIN 1. ANODE 2. CATHODE 3. GATE	STYLE 26: PIN 1. CATHODE 2. ANODE 3. NO CONNECTION
STYLE 27: PIN 1. CATHODE 2. CATHODE 3. CATHODE	STYLE 28: PIN 1. ANODE 2. ANODE 3. ANODE				

DOCUMENT NUMBER:	98ASB42226B	Electronic versions are uncontrolled except when accessed directly from the Document Repositor Printed versions are uncontrolled except when stamped "CONTROLLED COPY" in red.		
DESCRIPTION:	SOT-23 (TO-236)		PAGE 2 OF 2	

onsemi and ONSEMi are trademarks of Semiconductor Components Industries, LLC dba onsemi or its subsidiaries in the United States and/or other countries. onsemi reserves the right to make changes without further notice to any products herein. onsemi makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does onsemi assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. onsemi does not convey any license under its patent rights nor the rights of others.

onsemi, Onsemi, and other names, marks, and brands are registered and/or common law trademarks of Semiconductor Components Industries, LLC dba "onsemi" or its affiliates and/or subsidiaries in the United States and/or other countries. onsemi owns the rights to a number of patents, trademarks, copyrights, trade secrets, and other intellectual property. A listing of onsemi's product/patent coverage may be accessed at www.onsemi.com/site/pdf/Patent-Marking.pdf. Onsemi reserves the right to make changes at any time to any products or information herein, without notice. The information herein is provided "as-is" and onsemi makes no warranty, representation or guarantee regarding the accuracy of the information, product features, availability, functionality, or suitability of its products for any particular purpose, nor does onsemi assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. Buyer is responsible for its products and applications using onsemi products, including compliance with all laws, regulations and safety requirements or standards, regardless of any support or applications information provided by onsemi. "Typical" parameters which may be provided in onsemi data sheets and/or specifications can and do vary in different applications and actual performance may vary over time. All operating parameters, including "Typicals" must be validated for each customer application by customer's technical experts. onsemi does not convey any license under any of its intellectual property rights nor the rights of others. onsemi products are not designed, intended, or authorized for use as a critical component in life support systems or any FDA class 3 medical devices with a same or similar classification in a foreign jurisdiction or any devices intended for implantation in the human body. Should Buyer purchase

ADDITIONAL INFORMATION

TECHNICAL PUBLICATIONS:

 $\textbf{Technical Library:} \ \underline{www.onsemi.com/design/resources/technical-documentation}$

onsemi Website: www.onsemi.com

ONLINE SUPPORT: www.onsemi.com/support

For additional information, please contact your local Sales Representative at

www.onsemi.com/support/sales